

# SCTMU001F

## **N-channel SiC power MOSFET**

$V_{\mathrm{DSS}}$	400V
R <sub>DS(on)</sub> (Typ.)	120m $Ω$
I <sub>D</sub>	20A
$P_D$	132W

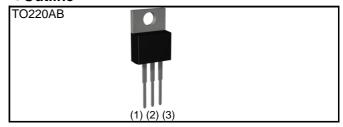
#### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

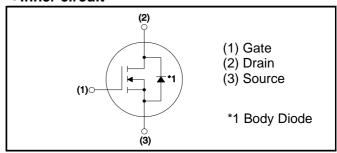
# Application

Audio

### Outline



### •Inner circuit



Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Tuno	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	50
	Taping code	-
	Marking	SCTMU001F

### ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{DSS}$	400	V	
Continuous drain current $T_c = 25^{\circ}C$	I <sub>D</sub> <sup>*1</sup>	20	А	
Pulsed drain current	I <sub>D,pulse</sub> *2			
Gate - Source voltage	$V_{GSS}$	-6 to 22	V	
Power dissipation $(T_c = 25^{\circ}C)$	$P_D$	132	W	
Junction temperature	T <sub>j</sub>	150	°C	
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C	

### ●Thermal resistance

Parameter	Symbol	Values			Unit
raiametei	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}$	-	0.72	0.95	°C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>	-	-	265	°C

# •Electrical characteristics ( $T_a = 25^{\circ}C$ )

Parameter	Symbol	Conditions	Values			Unit
raiailletei	Symbol Conditions —		Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	400	-	-	V
		$V_{DS} = 400V, V_{GS} = 0V$				
Zero gate voltage drain current	$I_{ m DSS}$	T <sub>j</sub> = 25°C	-	0.1	1	μΑ
drain ourront		T <sub>j</sub> = 150°C	-	0.5	-	
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I <sub>GSS-</sub>	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 3.3 \text{mA}$	1.6	-	4.0	V
		$V_{GS} = 18V, I_D = 10A$				
Static drain - source on - state resistance	R <sub>DS(on)</sub> *3	T <sub>j</sub> = 25°C	-	120	156	mΩ
on state resistance		T <sub>j</sub> = 100°C	-	137	-	
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	14	-	Ω

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*2</sup> PW  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

<sup>\*3</sup> Pulsed

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g <sub>fs</sub> *3	$V_{DS} = 10V, I_{D} = 10A$	-	2.7	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	1218	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 200V	-	102	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	ı	14	ı	
Turn - on delay time	t <sub>d(on)</sub> *3	$V_{DD} = 300V, I_{D} = 5A$	ı	22	1	
Rise time	t <sub>r</sub> *3	V <sub>GS</sub> = 18V/0V	ı	23	ı	ne
Turn - off delay time	t <sub>d(off)</sub> *3	$R_L = 60\Omega$		67		ns
Fall time	t <sub>f</sub> *3	$R_G = 0\Omega$	-	30	-	

# •Gate Charge characteristics $(T_a = 25^{\circ}C)$

Parameter	Symbol Conditions -	Conditions	Values			Unit
		Min.	Тур.	Max.	Offic	
Total gate charge	$Q_g^{*3}$	V <sub>DD</sub> = 200V	-	59	-	
Gate - Source charge	$Q_{gs}^{*3}$	I <sub>D</sub> = 5A	-	13	ı	nC
Gate - Drain charge	Q <sub>gd</sub> *3	V <sub>GS</sub> = 18V	-	18	-	

# ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol Conditions	Conditions		Values		
		Conditions	Min.	Тур.	Max.	Unit
Inverse diode continuous, forward current	I <sub>S</sub> *1	T <sub>c</sub> = 25°C	-	-	20	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2		ı	-	60	А
Forward voltage	$V_{SD}^{*3}$	$V_{GS} = 0V, I_{S} = 10A$	-	4.3	-	V
Reverse recovery time	t <sub>rr</sub> *3	$I_F = 10A$ , $V_R = 400V$ di/dt = 165A/ $\mu$ s	-	29	-	ns
Reverse recovery charge	Q <sub>rr</sub> *3		-	53	-	nC
Peak reverse recovery current	I <sub>rrm</sub> *3		ı	3.1	-	Α

Fig.1 Power Dissipation Derating Curve

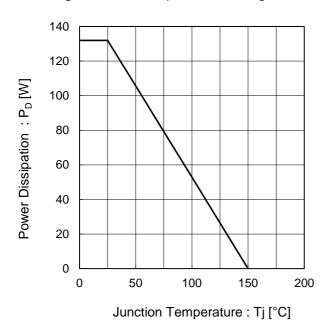
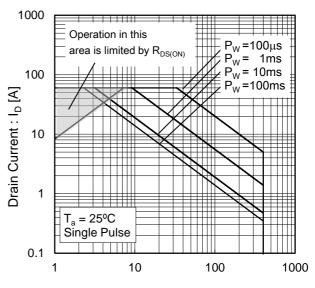


Fig.2 Maximum Safe Operating Area



Drain - Source Voltage :  $V_{DS}$  [V]

Fig.3 Typical Transient Thermal Resistance vs. Pulse Width

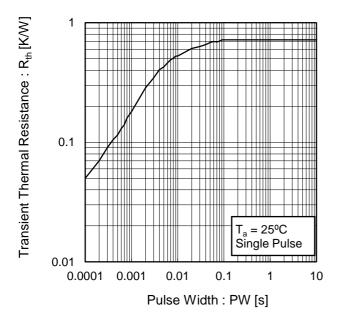


Fig.4 Typical Output Characteristics

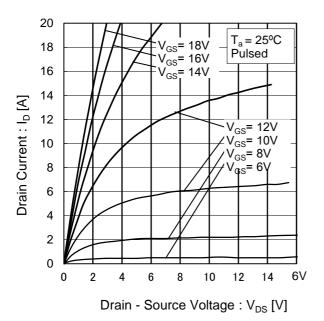


Fig.5 Tj = 150° C Typical Output Characteristics

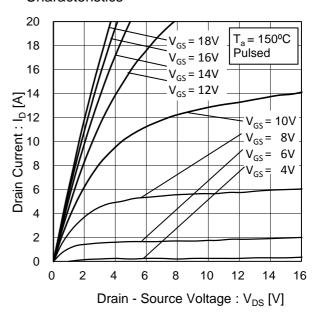
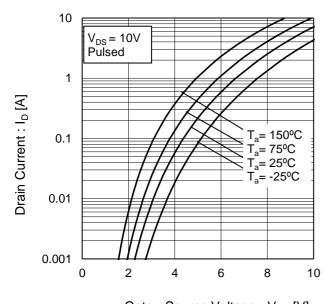
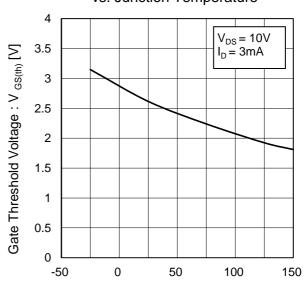


Fig.6 Typical Transfer Characteristics



Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.7 Gate Threshold Voltage vs. Junction Temperature



Junction Temperature :  $T_j$  [°C]

Resistance vs. Gate - Source Voltage Static Drain - Source On-State Resistance 0.5  $T_a = 25^{\circ}C$ Pulsed 0.4  $:R_{\mathsf{DS}(\mathsf{on})}\left[ \Omega \right]$ 0.3 0.2  $I_{D} = 10A$ 0.1 0 22 6 8 10 12 16 18 20

Fig.8 Static Drain - Source On - State

Fig.9 Static Drain - Source On - State Resistance vs. Junction Temperature

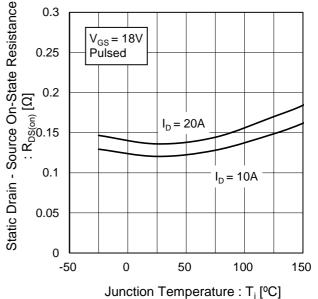


Fig.10 Static Drain - Source On - State Resistance vs. Drain Current

Gate - Source Voltage : V<sub>GS</sub> [V]

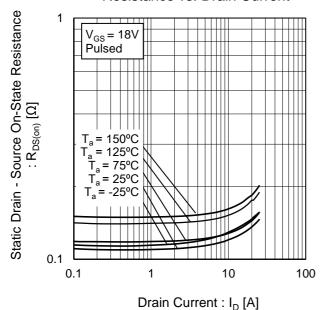


Fig.11 Transconductance vs. Drain Curren

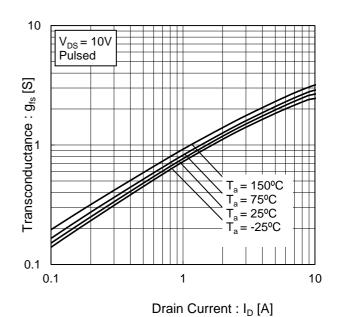


Fig.12 Typical Capacitance vs. Drain - Source Voltage

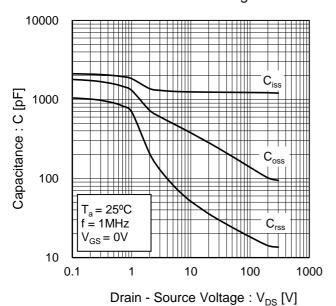


Fig.13 Dynamic Input Characteristics

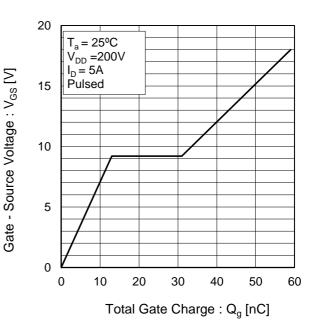
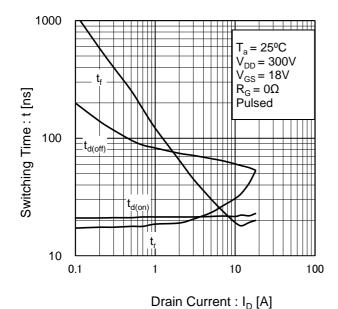


Fig.14 Switching Characteristics



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### ●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

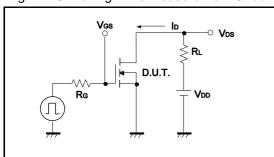


Fig.2-1 Gate Charge Measurement Circuit

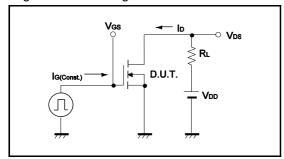


Fig.1-2 Switching Waveforms

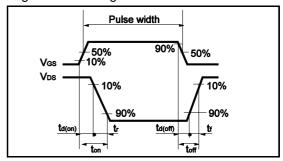
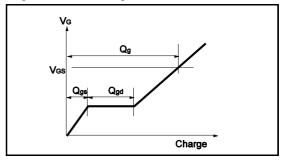
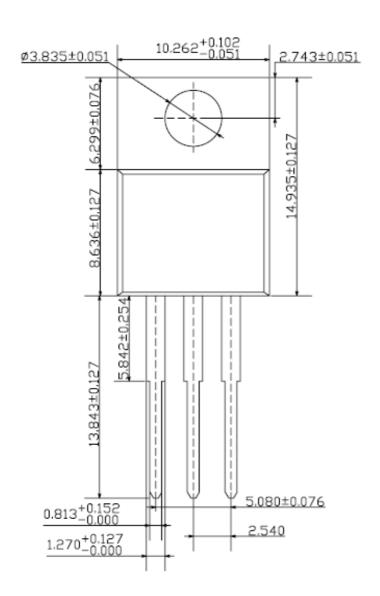


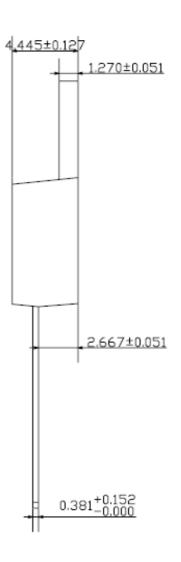
Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)

### **TO-220AB**







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